## Tight-binding study of structure and vibrations of am orphous silicon

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W e present a tight-binding calculation that, for the st time, accurately describes the structural, vibrational and elastic properties of am orphous silicon. We compute the interatom ic force constants and nd an unphysical feature of the Stillinger-W eber empirical potential that correlates with a much noted error in the radial distribution function associated with that potential. We also nd that the intrinsic st peak of the radial distribution function is asymmetric, contrary to usual assumptions made in the analysis of di raction data. We use our results for the normal mode frequencies and polarization vectors to obtain the zero-point broadening e ect on the radial distribution function, enabling us to directly compare theory and a high resolution x-ray di raction experiment.

PACS num bers: 61.43 D q, 62.20 D c, 63.50.+ x, 78.55 Q r

Am orphous silicon (a-Si) is a prototype for continuousrandom -network covalent glasses that, with som e hydrogen content, has technological applications as a relatively inexpensive electronic material. W hile the basic structure of a-Si is believed to be a four-fold-coordinated continuous random network, detailed inform ation about network connectivity and defects is lacking. A tom ic resolution structure is very di cult to determ ine directly, and experiments have relied on unusual or indirect probes such as variance coherence microscopy [1] and Raman spectroscopy [2, 3] as well as on more standard techniques such as di raction [4, 5] and EXAFS [6, 7]. The experim entalm easurem ents suggest signi cant deviation from a continuous random network, including average coordination that is signi cantly less than 4 (e.g. Ref.5) and that unannealed sam ples m ay be paracrystalline [1]. M any empirical-potential simulations have been done, but it is not clear if empirical potentials are accurate enough to give reliable results for properties, such as coordination defects, that depend on bond breaking and bond form ation. A number of simulations of a-Sistructure have used electronic-structure based m ethods, w hich are generally am ong the most reliable for solid state system s (e.g. Refs. 8, 9, 10, 11). How ever, none have carefully compared the radial distribution function (RDF) to high resolution experiments [5], and none included quantum -m echanical vibrationale ects. A nother im portant question concerns the vibrational properties of a-Si, which give us information about the structure and the interactions of atom s in the material. The vibrational density of states (VDOS) was measured experimentally using inelastic neutron scattering (INS) [32]. Empiricalpotential simulations have been used to analyze vibrational properties in detail [12], but all show signi cant errors in the shape of the VDOS or in other properties. W hile the VDOS of a-Si has been simulated with electronic structure m ethods [8, 13, 14], the underlying force constants them selves have not been analyzed. There have been many studies of force constants in crystalline Si, which shows unusual phonon dispersion and force constants that oscillate in magnitude as a function of distance [15, 16].

W e study the elastic constants, vibrational properties, and structure of a-Si using a tight-binding (TB) totalenergy m ethod. W e nd elastic constants and VDOS that are in good agreem ent with experim ent, and qualitatively better than empirical-potential simulations. The structure has a sharp rst-neighbor RDF peak that agrees very well with experim ent when zero-point and therm al broadening is included. This peak is signi cantly non-G aussian, calling into question the coordination-statistics analysis of previous di raction experim ents.

We use the Naval Research Laboratory (NRL) TB m ethod [17, 18]. The non-orthogonalsp<sup>3</sup>-basis TB m odel has been shown to accurately describe the elastic constants and phonon dispersion in crystalline Si and the electronic density of states for a highly defected am orphous model [18]. To generate the a-Simodels we relax using TB-calculated forces a-Sim odels generated by other techniques. The NRL-TB model is used to calculate the energy of the structure and the atom ic forces [21]. The conjugate-gradient method is applied to nd mechanical-equilibrium positions at a xed volum e, em ploying the criterion that com ponents of atom ic forces be less than 10  $^3\,$  eV /A . The relaxation procedure is carried out at several volum es to obtain results at zero pressure, but components of the stress tensor, generally of m agnitude less than 0.8 GPa, rem ain.

O ne m odel, which we denote TB1, is generated by relaxing (using TB) a 216 atom perfect continuous-random – network m odel [19] with periodic boundary conditions relaxed with a K eating interatom ic potential [20]. The TB-relaxed m odel is perfectly four-fold coordinated, with 1.3% lower density than the crystal, compared to 1.7% lower density m easured experimentally [5]. The bondangle distribution has a RMS deviation of 11 from the average value of 109.2, in close agreement with relaxed ab initio calculation [10] and analysis of experiment [4]. A second m odel, which we denote TB2, is generated by relaxing a structure from a molecular-dynam ics simulation

TABLE I: Selected elastic constants c, bulk modulus B and Young's modulus E  $(10^{11} \text{ dyn/cm}^2)$ . The index i varies from 1 to 3, and j from 4 to 6.

	TB1	TB2	Exp./FP	SW <sup>(a)</sup>
$C_{ii}$	16.31-16.45	15.06-16.00	13.8 <sup>(b)</sup> ,17(2) <sup>(c)</sup>	11.94-13.11
Cjj	5.68-5.84	5.26-5.56	4.8 <sup>(b)</sup> , 4.5 <sup>(a)</sup>	2.54-3.21
Cp <sup>(d)</sup>	5.77	5.06	"	2.62
C <sub>12</sub>	4.77	5.32		6.69
В	8.73	8.99	5.9 <sup>(e)</sup> ,8.25 <sup>(f)</sup>	8.52
Е	14 <sup>(g)</sup>	13 <sup>(g)</sup>	12.4 (3) <sup>(a)</sup>	7 <sup>(g)</sup>
			11.7 (5)–13.4 (5) <sup>(h)</sup>	

(a) Ref. 24; (b) Ref. 25; (c) Ref. 26;

(d) D e ned here as  $(c_{11}-c_{12})/2$ ; (e) R ef. 27

(f) Ref. 10; (g) based on values of  $c_{12}$  and  $c_p$ ;

(h) Ref. 28.

of the rapid quenching of liquid Siusing the environm ent dependent interatom ic potential [22]. The TB2 structure is slightly more dense than TB1, but still about 0.5% less dense than the crystal. The energy is 28 m eV / atom low er than the TB1 energy, despite the presence of 6% 5-fold and 0.46% 3-fold coordinated atom s (corresponding to an average coordination of 4.05) [23]. The RM S bond-angle deviation is 12.5, although the distribution has wide, non-Gaussian wings; excluding 2% of the bond-angles reduces the RMS deviation to 10.4 . We also show some com parisons with results using the Stillinger-Weber (SW) interatom ic potential [29]. The SW potential, which includes radial and bond-angle term s, is one of the most often used potentials for simulations of Si. We use a structure (Ref. 24, Table II, model IV) generated by relaxing with SW the same starting structure as TB1. Finally, we note that while it is possible to use electronic structure m ethods to generate am orphous structures from procedures that are less dependent on the initial structure, it is very expensive computationally. The di culty in fully annealing the structure seems to lead to a consistent overestim ate of the width of the st-neighbor peak in the RDF [8, 9].

The relaxed static lattice TB elastic constants  $c_{ij}$  were obtained by the method of hom ogeneous deformation. The TB results [31] are compared in Table I with results of rst-principles (FP) [0] calculations, SW calculations, and several experiments on dense samples (a wider range of shear values are quoted in Table V of Ref. 30). Although there is some deviation between the two TB structures it is small. W hile ultrasonicm easurements of elastic properties are not available for a-Si, the Young'sm odulus E can be measured with a vibrating reed apparatus, and other elastic constants can be inferred from spectroscopic studies. O ur TB results for both models are close to the experimental values, although our value of  $c_{44}$  is likely 10{20% too large. The SW empirical potential results are signic cantly worse in comparison with experiment.

The VDOS is calculated from a dynamical ma-

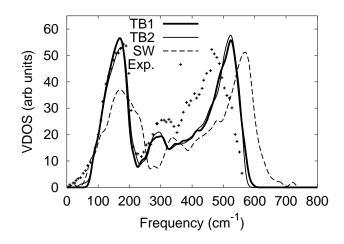
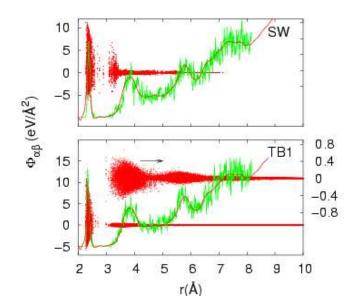


FIG.1: V ibrational density of states of a-Si. A Gaussian broadening of FW H M = 20 cm  $^{1}$  is employed. The experim ental data are from Ref. [32].

trix approach. The matrix elements (i;j) F (i)= u (j) are calculated using the TB forces with a central-nite di erence approach that elim inates alloddorder anham onic term s in the potential energy [33]. The TB VDOS for structures TB1 and TB2 are compared with SW results and INS [32] measurements in Fig. 1. For both structures the TB calculation yields the overall shape very well; it exactly describes the low frequency TA peak, gives a slightly too sm all frequency of the LA peak (300 cm<sup>-1</sup>) and about a 10% percent too high frequency of the high frequency TO peak. The TB results are a qualitative improvement over results based on the SW potential, as shown in the gure, and they are in good agreem ent with ab initio results for a 216 atom structural m odel [14].

The range of the e ective interactions in the solid can give us inform ation about the physics of the interactions, and can guide the developm ent of approxim ations such as em pirical potentials. In Fig. 2 we plot all of the cartesian force constants between pairs of atom swith interatom ic distances less than 10 A. The di erence in range between the SW results and the TB results is easy to see: The SW interactions are large up to about 3.5 A, and go to exactly zero at twice the SW cuto of 3.75A. The TB interactions are already quite sm all at 2.8 A, but do not go to zero even at 10 A. This com parison of TB and SW leads to a view of interactions in the solid that is more subtle than the usual assumption that empirical potentials are short ranged and that the real interactions are long ranged: The SW potential interactions go to zero at a range that is too short, but at interm ediate distances the interactions are too strong. We also note that the preponderance of force constants as a function of interatom ic distance give a clear envelope function that has an oscillatory behavior which m atches the RDF peak positions. This is qualitatively similar to the case of the crystal,



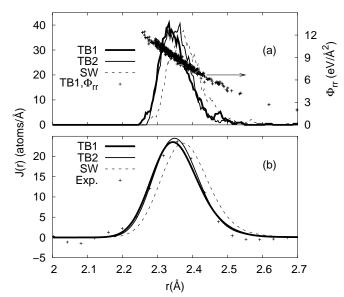


FIG.2: Force constants between pairs of atom s in SW (top) and TB1 (bottom) relaxed structures (dots). Superim posed are the corresponding J (r) functions (jagged lines) in arbitrary units and the experim ental, annealed-sam ple, results of R ef. [5] for J (r) (sm ooth lines). The upper scatterplot in the TB panel is a m agni cation of the sm aller m agnitude force constants.

even though the explanations for the oscillation in the crystaldo not apply to the am orphous structure [15, 16].

The problem with the SW potential is a direct consequence of the form of the potential. In the am orphous there are pairs of atom s in the second-neighbor peak with distances smaller than the SW cuto . It is clear from the TB force constants that the e ective interactions for these pairs is qualitatively di erent from the rstneighbor interactions. However, in the SW simulation these second-neighbor pairs interact through term s that are meant to describe the interactions of rst-neighbor atoms. In particular, the two-body contribution has strong negative curvature at these distances, and the three-body term s include contributions from triplets with a vertex angle that does not correspond to an atom with two sp<sup>3</sup> orbitals in bonding con gurations. These two types of contributions lead to the unphysically large force constants in the SW results at this range of distances. The range of incorrect force constants also coincides with the shoulder in the SW RDF that is not observed in our TB results or in the experim entalm easurem ents [34].

The distribution of force constants gives us inform ation about the types of elective interactions between bonded atom s. Under the inst peak of the RDF the largest positive cartesian force constants are twice the magnitude of the largest negative force constants for both SW and TB. This relation is consistent with an elective bondstretching interaction for inst-neighbors. We plot the results for the bond-stretching components in a plot as

FIG. 3: (a) First peak of the static RDF and TB1 bond stretching force constants. (b) B roadened results corresponding to T = 10K in comparison with experiment (annealed sample).[5]

a function of r (Fig. 3a). The radial force constants decrease with increasing r as one expects from a physically reasonable rst-neighbor bonding potential. Pairs with large (sm all) interatom ic bond stretching force constants will have sm all (large) relative mean square displacements, so these results clearly have an impact on the nature of the broadening of the RDF.

Very little attention has been given in the literature to the shape of the rst peak in the RDF J (r) §5]. This peak has been m easured very carefully at T = 10 K with x-ray di raction, using high energy photons and high resolution, i.e., large Q<sub>max</sub>, by Laaziriet al. [5]. They obtain a t of their data to a Gaussian, with average coordination of 3.88 :01 (3.79 :01) for the annealed (unannealed) sample. In Fig. 3a we plot the st peak of the static J(r) for models TB1 and TB2, and the SW results. The TB static peak is asymmetric, and its width is signi cantly larger than the static-disorder estim ate by Laaziri et al. In order to compare directly with the experim ental J (r) it is necessary to properly take account of the zero-point and therm al broadening. The quantity measured by the x-ray experiment is, in the smalldisplacem ent lim it,

$$J(r) = \frac{1}{N} \frac{X^{N}}{\sum_{i,j=1}^{r} \frac{1}{2 U_{ij}^{r}} \exp((r_{ij} r)^{2} = (2U_{ij}^{r}));$$

where  $U_{ij}^r h(\hat{r}_{ij} \ \underline{u}_j)^2 i$ . Thus we need the mean-squared relative displacements, for pairs of atom s, along the interatom ic vector direction. We calculate them within the harm onic approximation at T = 10 K using

our computed vibrationalmodes. Since T = 10 K essentially corresponds to T = 0 K for these considerations, what we obtain is the minimum measurable width for the rst peak in the RDF of am orphous silicon. As seen in Fig. 3b the results are in agreement with experiment, aside from a small skewing of the theoretical function to large r. Although it has not been observed in a-Si, this type of asymmetry has been observed in EXAFS of am orphous germanium [36]. Both the TB1 and TB2 models, despite the very diment originating structure and dimensional defects, show nearly identical RDF

rst peaks. The good agreem ent with experim ent of the broadened RDF suggests that our static peak width is correct, and that Laaziri et al. underestim ate the static disorder contribution to the broadening. This may be caused by inaccuracy in the polycrystalline J (r) that is used to estim ate the dynam ic broadening. In the experim ents a low erQ<sub>m ax</sub> (35 A<sup>1</sup>) was used for the polycrystal than for the am ophous structure (55 A<sup>1</sup>), although the form er is expected to have a narrow er rst peak. Num erous other treatm ents using EXAFS or di raction have not been considered here because they all use too low values of Q<sub>m ax</sub> for obtaining reliable inform ation on the

rst peak. The only other theoretical study of quantum e ects in J (r) is by Herrero  $\beta 5$ ], who used the SW potential but treated the quantum -e ects on the nuclear vibrations exactly. Our results using the SW potential are presented in Fig. 3. The result for the amount of zero-point broadening is consistent with Herrero's work, although due to di ering approximations a direct com parison is not possible. We note that the W ooten m odel on which both the SW and TB1 m odels are based yields a static J (r) (not shown) that is quite symmetric, and as broad as the experimental breadth.

To conclude, we have show n that the NRL-TB m ethod can reliably compute structural, vibrational, and elastic properties of a-Si. The results are nearly identical for two structuralm odels, one with perfect four-fold coordination and one with several atom ic percent coordination defects. We have presented the rst discussion of force constants in a-Si, which has revealed limitations of the m ost frequently used empirical potential for silicon. O ur calculated elastic constants fall within the range of experimental values for imperfect sam ples prepared under various conditions. We have also carefully studied the

rst peak in the radial distribution function. We observe a clear asymmetric peak in the case of the static quantity which is not observable experimentally. We have included the (essentially) zero-point broadening e ects in J (r) to obtain the experimentally measured quantity. O ur two structural models, which have average coordinations of 4.00 and 4.05, respectively, reproduce the rst peak in the experimental J (r) (for the annealed sam – ple) except for a slight asymmetry still present in the broadened result. We believe that such an asymmetry is expected on physical grounds and that perhaps it has been  $\mbox{missed}$ " experimentally because of the challenging analysis required to obtain J (r) from the diraction results.

This work was supported by the U.S.O  $\infty$  of N aval Research. We are also grateful to Dr. S. Roorda for a helpful communication and for sending us the x-ray data of Ref. [5] for the radial distribution function. We thank Dr. S. Richardson for a helpful conversation.

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